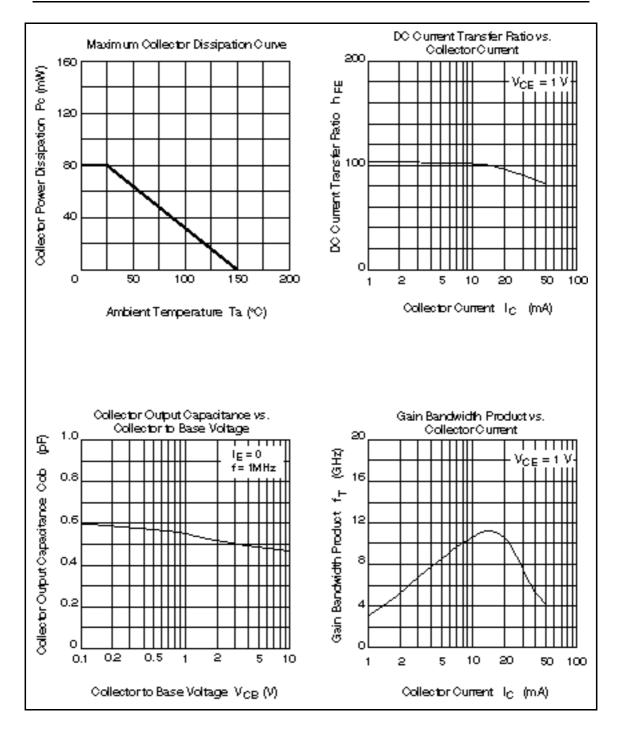


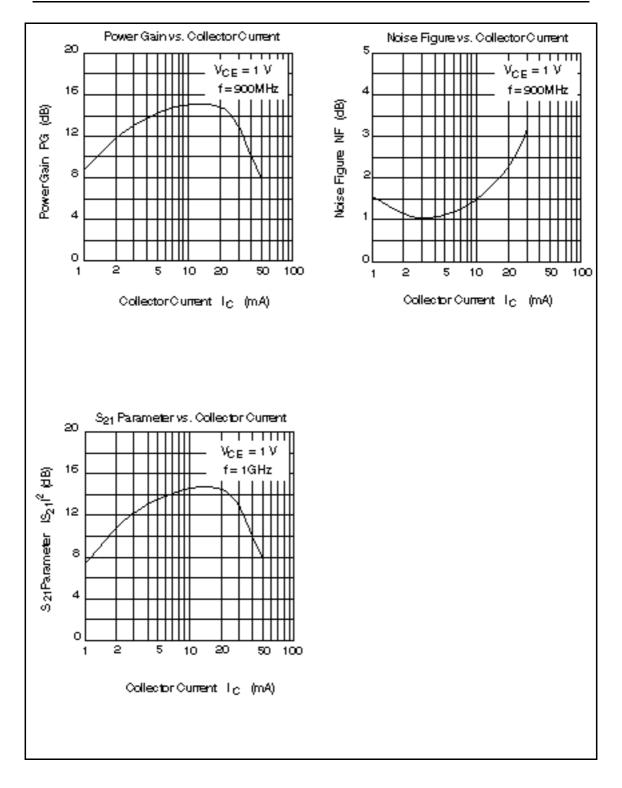
## **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

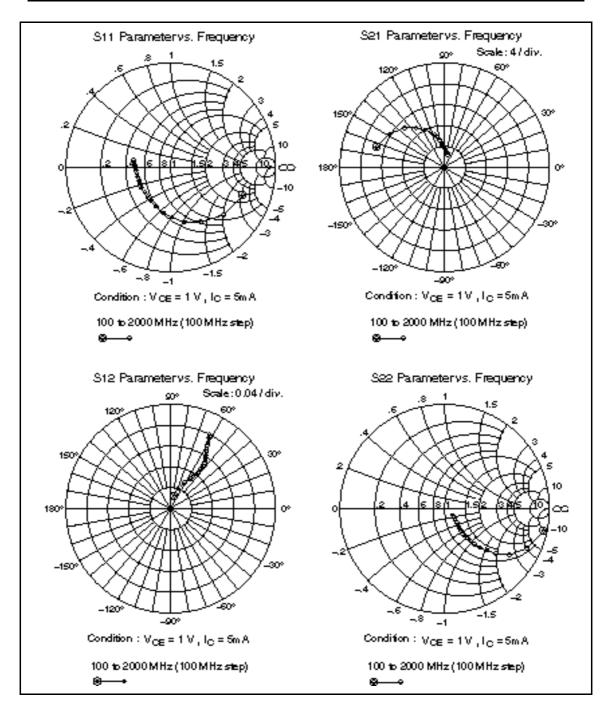
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	15	V
Collector to emitter voltage	V <sub>CEO</sub>	8	V
Emitter to base voltage	V <sub>EBO</sub>	1.5	V
Collector current	I <sub>c</sub>	50	mA
Collector power dissipation	Pc	80	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

# **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Мах	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_{\rm C}=10\mu A$ , $I_{\rm E}=0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μA	$V_{CB} = 12V$ , $I_E = 0$
Collector cutoff current	I <sub>ceo</sub>	_	_	1	mA	$V_{ce} = 8V$ , $R_{be} =$
Emitter cutoff current	I <sub>EBO</sub>	_	_	10	μA	$V_{\text{EB}} = 1.5 V$ , $I_{\text{C}} = 0$
DC current transfer ratio	$h_{\text{FE}}$	50	100	160	V	$V_{ce} = 1V$ , $I_c = 5mA$
Collector output capacitance	Cob	—	0.55	0.85	pF	$V_{CB} = 1V$ , $I_E = 0$ f = 1MHz
Gain bandwidth product	f <sub>T</sub>	6	9	_	GHz	$V_{ce} = 1V$ , $I_c = 5mA$
Power gain	PG	11	14	_	dB	$V_{CE} = 1V, I_C = 5mA$ f = 900MHz
Noise figure	NF	_	1.1	2.0	dB	$V_{CE} = 1V, I_{C} = 5mA$ f = 900MHz



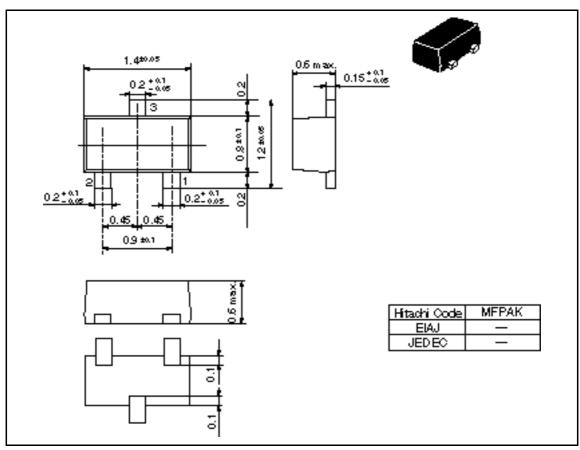




	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.734	-21.4	13.62	163.7	0.0220	78.7	0.956	-13.4
200	0.676	-41.9	12.34	148.7	0.0421	69.3	0.865	-25.5
300	0.598	-59.8	10.79	136.0	0.0572	61.9	0.753	-34.7
400	0.530	-75.6	9.38	126.5	0.0678	57.2	0.652	-41.0
500	0.471	-88.8	8.18	118.9	0.0756	55.0	0.568	-45.4
600	0.429	-100.8	7.19	112.9	0.0821	53.9	0.498	-48.3
700	0.395	-110.8	6.40	107.8	0.0881	53.4	0.442	-50.2
800	0.370	-120.6	5.74	103.5	0.0940	53.4	0.395	-51.7
900	0.349	-130.0	5.20	100.1	0.0990	54.0	0.355	-52.3
1000	0.336	-136.4	4.74	96.9	0.104	54.6	0.323	-52.7
1100	0.332	-144.1	4.39	93.9	0.109	55.5	0.294	-52.9
1200	0.327	-151.6	4.05	91.4	0.115	56.4	0.270	-52.8
1300	0.322	-157.0	3.77	89.1	0.120	57.4	0.250	-52.2
1400	0.325	-162.9	3.54	86.9	0.125	58.0	0.230	-52.6
1500	0.322	-168.0	3.32	84.9	0.130	58.8	0.215	-52.0
1600	0.331	-172.6	3.14	82.7	0.138	59.8	0.200	-51.5
1700	0.338	-177.0	2.97	80.9	0.143	60.3	0.185	-51.5
1800	0.337	179.0	2.84	79.4	0.149	61.5	0.171	-51.2
1900	0.341	175.4	2.71	77.9	0.154	61.7	0.158	-51.1
2000	0.358	170.8	2.59	76.0	0.161	62.4	0.147	-50.9

# Sparameter (V $_{CE}$ = 1V, $I_{C}$ = 5mA, Zo = 50 $\,$ )

## **Package Dimensions**



Unit: mm

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